512 Kbit / 1 Mbit / 2 Mbit / 4 Mbit (x8) Many-Time Programmable Flash

SST37VF512 / SST37VF010 / SST37VF020 / SST37VF040

Data Sheet

FEATURES:

- **Organized as 64K x8 / 128K x8 / 256K x8 / 512K x8**
- **2.7-3.6V Read Operation**
- **Superior Reliability**
  - Endurance: At least 1000 Cycles
  - Greater than 100 years Data Retention
- **Low Power Consumption**
  - Active Current: 10 mA (typical)
  - Standby Current: 1 µA (typical)
- **Fast Read Access Time**
  - 70 and 90 ns
- **Fast Byte-Program Operation**
  - Byte-Program Time: 10 µs (typical)
  - Chip-Program Time:
    0.6 seconds (typical) for SST37VF512
    1.2 seconds (typical) for SST37VF010
    2.4 seconds (typical) for SST37VF020
    4.8 seconds (typical) for SST37VF040
- **Electrical Erase Using Programmer**
  - Does not require UV source
  - Chip-Erase Time: 100 ms (typical)
- **CMOS I/O Compatibility**
- **JEDEC Standard Byte-wide Flash EEPROM Pinouts**
- **Packages Available**
  - 32-Pin PDIP
  - 32-Pin PLCC
  - 32-Pin TSOP (8mm x 14mm)

PRODUCT DESCRIPTION

The SST37VF512/010/020/040 devices are 64K x8 / 128K x8 / 256K x8 / 512K x8 CMOS, Many-Time Programmable (MTP), low cost flash, manufactured with SST's proprietary, high performance CMOS SuperFlash technology. The split-gate cell design and thick oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches. The SST37VF512/010/020/040 can be electrically erased and programmed at least 1000 times using an external programmer, e.g., to change the contents of devices in inventory. The SST37VF512/010/020/040 have to be erased prior to programming. These devices conform to JEDEC standard pinouts for byte-wide flash memories.

Featuring high performance Byte-Program, the SST37VF512/010/020/040 provide a typical Byte-Program time of 10 µs. Designed, manufactured, and tested for a wide spectrum of applications, these devices are offered with an endurance of at least 1000 cycles. Data retention is rated at greater than 100 years.

The SST37VF512/010/020/040 are suited for applications that require infrequent writes and low power nonvolatile storage. These devices will improve flexibility, efficiency, and performance while matching the low cost in nonvolatile applications that currently use UV-EPROMs, OTPs, and mask ROMs.

To meet surface mount and conventional through hole requirements, the SST37VF512/010/020/040 are offered in 32-pin PLCC, PDIP and TSOP packages. See Figures 1, 2 and 3 for pinouts.

Device Operation

The SST37VF512/010/020/040 devices are nonvolatile memory solutions that can be used instead of standard flash devices if in-system programmability is not required. It is functionally (Read) and pin compatible with industry standard flash products.The device supports electrical Erase operation via an external programmer.

Read

The Read operation of the SST37VF512/010/020/040 is controlled by CE# and OE#. Both CE# and OE# have to be low for the system to obtain data from the outputs. Once the address is stable, the address access time is equal to the delay from CE# to output (T_{CE}). Data is available at the output after a delay of T_{OE} from the falling edge of OE#, assuming the CE# pin has been low and the addresses have been stable for at least T_{CE} - T_{OE}. When the CE# pin is high, the chip is deselected and a standby current of only 10 µA (typical) is consumed. OE# is the output control and is used to gate data from the output pins. The data bus is in high impedance state when either CE# or OE# is V_{IH}. Refer to Figure 4 for the timing diagram.

Byte-Program Operation

The SST37VF512/010/020/040 are programmed by using an external programmer. The programming mode is activated by asserting 12V (±5%) on OE# pin and V_{IL} on CE# pin. The device is programmed using a single pulse (WE# pin low) of 10 µs per byte. Using the MTP programming algorithm, the Byte-Program process continues byte-by-byte until the entire chip has been programmed. Refer to Figure 10 for the flowchart and Figure 6 for the timing diagram.

Chip-Erase Operation

The only way to change a data from a "0" to "1" is by electrical erase that changes every bit in the device to "1". The SST37VF512/010/020/040 use an electrical Chip-Erase operation. The entire chip can be erased in 100 ms (WE# pin low). In order to activate erase mode, the 12V (±5%) is applied to OE# and A_9 pins while CE# is low. All other address and data pins are "don't care". The falling edge of WE# will start the Chip-Erase operation. Once the chip has been erased, all bytes must be verified for FF. Refer to Figure 9 for the flowchart and Figure 5 for the timing diagram.

Product Identification Mode

The Product Identification mode identifies the devices as SST37VF512, SST37VF010, SST37VF020, and SST37VF040 and manufacturer as SST. This mode may be accessed by the hardware method. To activate this mode, the programming equipment must force V_H (12V±5%) on address A_9. Two identifier bytes may then be sequenced from the device outputs by toggling address line A_0. For details, see Table 3 for hardware operation.

TABLE 1: PRODUCT IDENTIFICATION TABLE

	Byte	Data
Manufacturer's Code	0000 H	BF H
Device Code		
SST37VF512	0001 H	C4 H
SST37VF010	0001 H	C5 H
SST37VF020	0001 H	C6 H
SST37VF040	0001 H	C2 H

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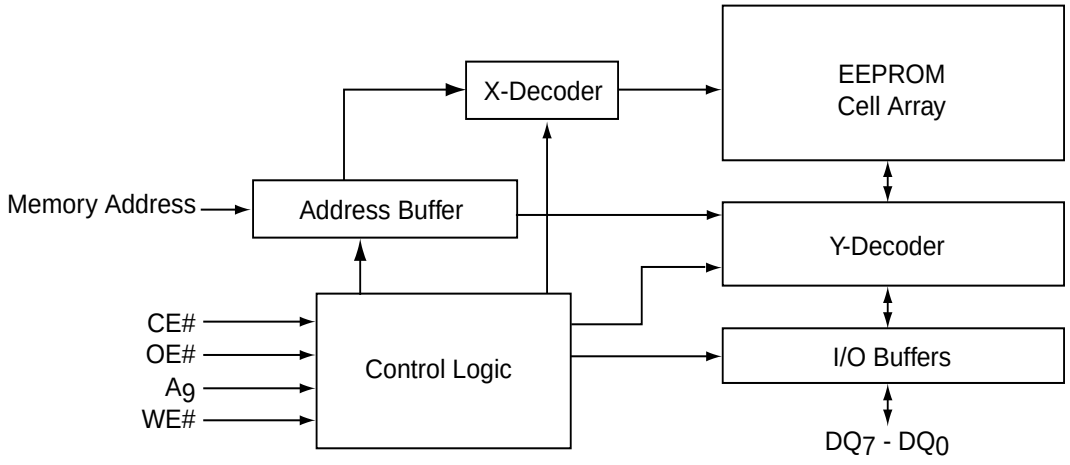
Design Considerations

The SST37VF512/010/020/040 should have a 0.1µF ceramic high frequency, low inductance capacitor connected between V_{DD} and GND. This capacitor should be placed as close to the package terminals as possible.

OE# and A_9 must remain stable at V_H for the entire duration of an Erase operation. OE# must remain stable at V_H for the entire duration of the Program operation.

FUNCTIONAL BLOCK DIAGRAM



397 ILL B1.0

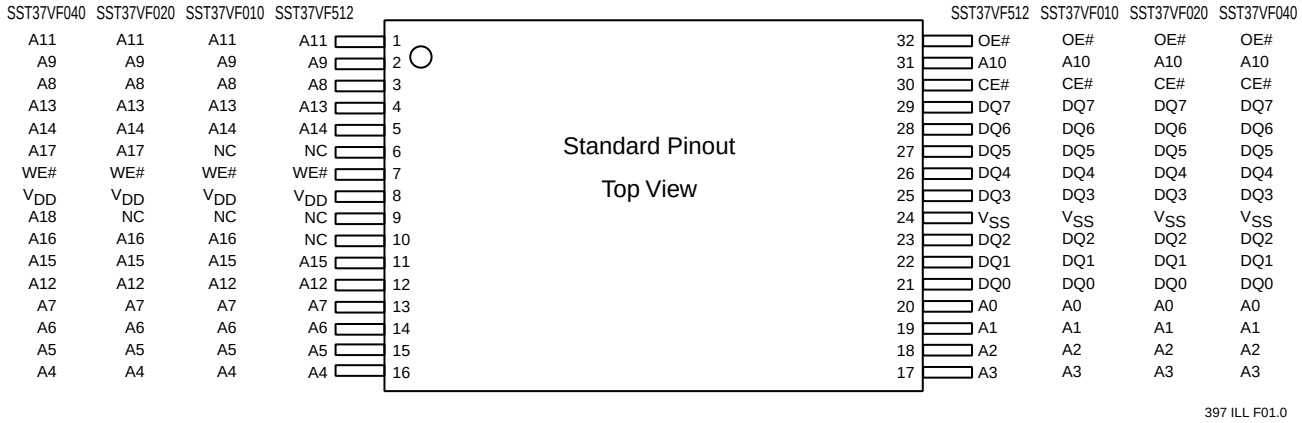


FIGURE 1: PIN ASSIGNMENTS FOR 32-PIN TSOP

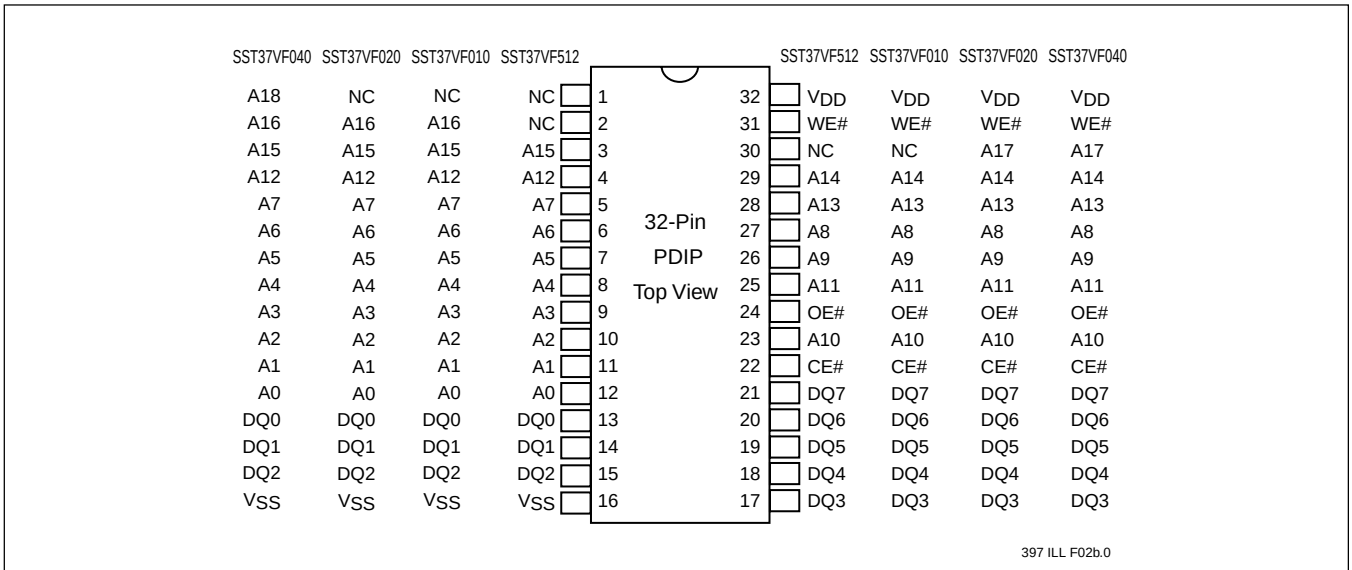


FIGURE 2: PIN ASSIGNMENTS FOR 32-PIN PDIP

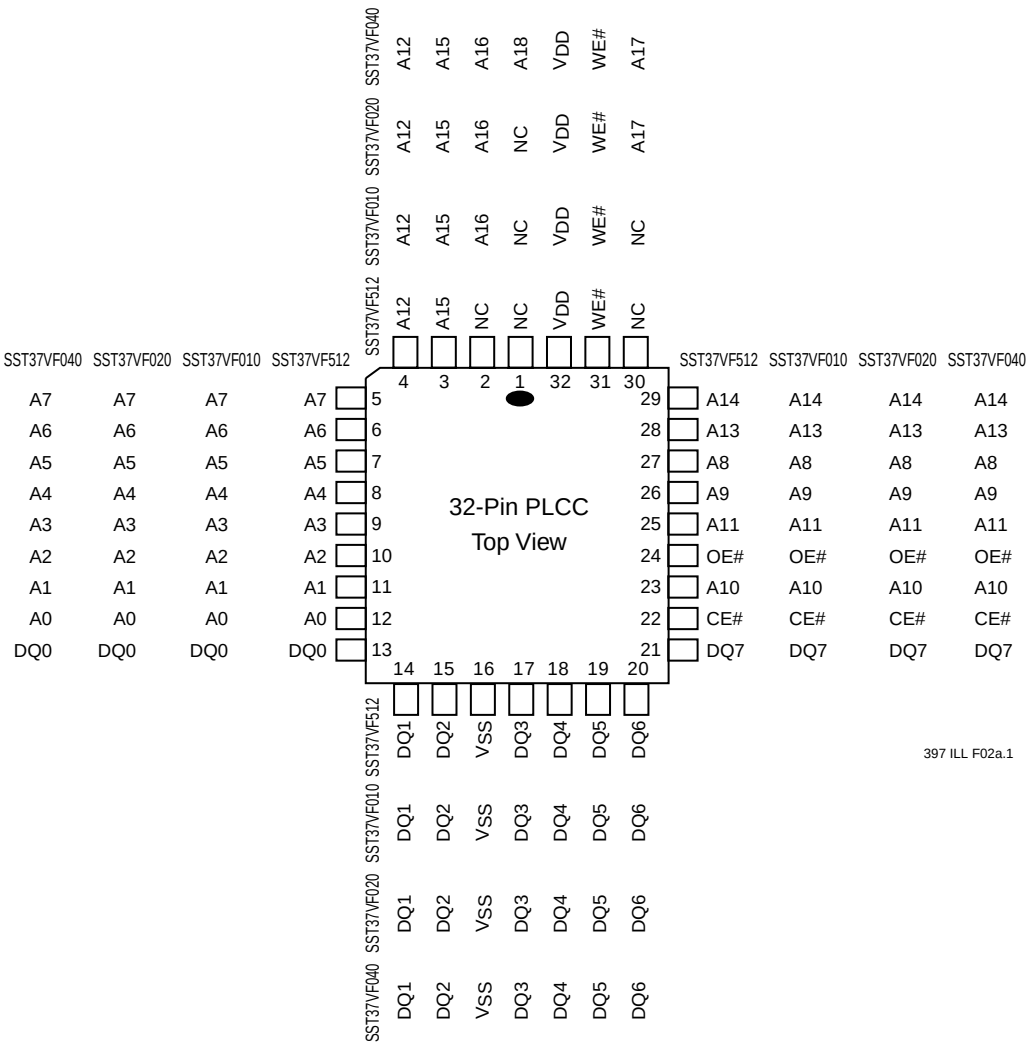


FIGURE 3: PIN ASSIGNMENTS FOR 32-PIN PLCC

TABLE 2: PIN DESCRIPTION

Symbol	Pin Name	Functions
A_{MS}-A_0	Address Inputs	To provide memory addresses
DQ_7-DQ_0	Data Input/Output	To output data during Read cycles and receive input data during Program cycle, the outputs are in tri-state when OE# or CE# is high.
CE#	Chip Enable	To activate the device when CE# is low
WE#	Write Enable	To program or erase (WE# = V_{IL} pulse during Program or Erase)
OE#	Output Enable	To gate the data output buffers during Read operation when low
V_{DD}	Power Supply	To provide 3-volt supply (2.7 to 3.6V)
V_{SS}	Ground	
NC	No Connection	Unconnected pins

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Note: A_{MS} = Most significant address
A_{MS} = A_{15} for SST37VF512, A_{16} for SST37VF010, A_{17} for SST37VF020 and A_{18} for SST37VF040.

TABLE 3: OPERATION MODES SELECTION

Mode	CE#	WE#	A_9	OE#	DQ	Address
Read	V_{IL}	V_{IH}	A_{IN}	V_{IL}	D_{OUT}	A_{IN}
Output Disable	V_{IL}	X	X	V_{IH}	High Z	A_{IN}
Standby	V_{IH}	X	X	X	High Z	X
Chip-Erase	V_{IL}	V_{IL}	V_H	V_H	High Z	X
Byte-Program	V_{IL}	V_{IL}	A_{IN}	V_H	D_{IN}	A_{IN}
Program/Erase Inhibit	X X	V_{IH} X	X X	X V_{IL} or V_{IH}	High Z High Z/D_{OUT}	X X
Product Identification	V_{IL}	V_{IH}	V_H	V_{IL}	Manufacturer Code (BF) Device Code (1)	A_{MS}(2)-A_1 = V_{IL}, A_0 = V_{IL} A_{MS}(2)-A_1 = V_{IL}, A_0 = V_{IH}

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Note: X = V_{IL} or V_{IH} (or V_H in case of OE# and A_9)
V_H = 12V±5%
(1) Device code C4 for SST37VF512, C5 for SST37VF010, C6 for SST37VF020 and C2 for SST37VF040.
(2) A_{MS} = Most significant address
A_{MS} = A_{15} for SST37VF512, A_{16} for SST37VF010, A_{17} for SST37VF020 and A_{18} for SST37VF040.

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute Maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias ..... -55°C to +125°C
Storage Temperature ..... -65°C to +150°C
D. C. Voltage on Any Pin to Ground Potential ..... -0.5V to V_{DD}+ 0.5V
Transient Voltage (<20 ns) on Any Pin to Ground Potential ..... -1.0V to V_{DD}+ 1.0V
Voltage on A_9 and OE# Pin to Ground Potential ..... -0.5V to 13.2V
Package Power Dissipation Capability (T_A = 25°C) 1.0W
Through Hole Lead Soldering Temperature (10 Seconds) ..... 300°C
Surface Mount Lead Soldering Temperature (3 Seconds) ..... 240°C
Output Short Circuit Current(1) ..... 50 mA

Note: (1) Outputs shorted for no more than one second. No more than one output shorted at a time.

OPERATING RANGE

Range	Ambient Temp	V_{DD}
Commercial	0°C to +70°C	2.7 to 3.6V
Industrial	-40°C to +85°C	2.7 to 3.6V

AC CONDITIONS OF TEST

Input Rise/Fall Time ..... 5 ns
Output Load ..... C_L = 100 pF
See Figures 7 and 8

TABLE 4: READ MODE DC OPERATING CHARACTERISTICS
V_{DD} = 2.7 to 3.6V, T_A = 0°C to 70°C (Commercial)

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I_{DD}	V_{DD} Read Current		12	mA	CE# = OE# = V_{IL}, all I/Os open, Address Input = V_{IL}/V_{IH}, at f = $1/T_{RC}$ Min, V_{DD} = V_{DD} Max
I_{SB}	Standby V_{DD} Current		15	µA	CE# = V_{IHC} V_{DD} = V_{DD} Max
I_{LI}	Input Leakage Current		1	µA	V_{IN} = GND to V_{DD}, V_{DD} = V_{DD} Max
I_{LO}	Output Leakage Current		1	µA	V_{OUT} = GND to V_{DD}, V_{DD} = V_{DD} Max
V_{IL}	Input Low Voltage		0.8	V	V_{DD} = V_{DD} Min
V_{IH}	Input High Voltage	0.7 V_{DD}		V	V_{DD} = V_{DD} Max
V_{IHC}	Input High Voltage (CMOS)	V_{DD}-0.3		V	V_{DD} = V_{DD} Max
V_{OL}	Output Low Voltage		0.2	V	I_{OL} = 100µA, V_{DD} = V_{DD} Min
V_{OH}	Output High Voltage	V_{DD}-0.2		V	I_{OH} = -100 µA, V_{DD} = V_{DD} Min
I_H	Supervoltage Current for A_9 for Read-ID		200	µA	CE# = OE# = V_{IL}, A_9 = V_H Max.

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TABLE 5: PROGRAM/ERASE DC OPERATING CHARACTERISTICS
V_{DD} = 2.7 to 3.6V, T_A = 25°C ± 5°C

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I_{DD}	V_{DD} Erase or Program Current		30	mA	CE# = V_{IL}, OE# = V_H, V_{DD} = V_{DD} Max, WE# = V_{IL}
I_{LI}	Input Leakage Current		1	µA	V_{IN} = GND to V_{DD}, V_{DD} = V_{DD} Max
I_{LO}	Output Leakage Current		1	µA	V_{OUT} = GND to V_{DD}, V_{DD} = V_{DD} Max
V_H	Supervoltage for A_9 and OE#	11.4	12.6	V	
I_H	Supervoltage Current for A_9 and OE#		200	µA	OE# = V_H Max, A_9 = V_H Max, V_{DD} = V_{DD} Max, CE# = V_{IL}

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TABLE 6: RECOMMENDED SYSTEM POWER-UP TIMINGS

Symbol	Parameter	Minimum	Units
$T_{PU-READ}$	Power-up to Read Operation	100	µs
$T_{PU-WRITE}$	Power-up to Write Operation	100	µs

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TABLE 7: CAPACITANCE (T_A = 25 °C, f=1 MHz, other pins open)

Parameter	Description	Test Condition	Maximum
$C_{I/O}$[1]	I/O Pin Capacitance	$V_{I/O}$ = 0V	12 pF
C_{IN}[1]	Input Capacitance	V_{IN} = 0V	6 pF

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Note: [1]This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 8: RELIABILITY CHARACTERISTICS

Symbol	Parameter	Minimum Specification	Units	Test Method
N_{END}	Endurance	1000	Cycles	JEDEC Standard A117
T_{DR}[1]	Data Retention	100	Years	JEDEC Standard A103
V_{ZAP_HBM}[1]	ESD Susceptibility Human Body Model	2000	Volts	JEDEC Standard A114
V_{ZAP_MM}[1]	ESD Susceptibility Machine Model	200	Volts	JEDEC Standard A115
I_{LTH}[1]	Latch Up	100 + I_{DD}	mA	JEDEC Standard 78

397 PGM T8.1

Note: [1] This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

AC CHARACTERISTICS

TABLE 9: READ CYCLE TIMING PARAMETERS

V_{DD} = 2.7 to 3.6V, T_A = 0°C to 70°C (Commercial)

		SST37VF512-70 SST37VF010-70 SST37VF020-70 SST37VF040-70		SST37VF512-90 SST37VF010-90 SST37VF020-90 SST37VF040-90		
Symbol	**Parameter**	**Min**	**Max**	**Min**	**Max**	**Units**
T_{RC}	Read Cycle Time	70		90		ns
T_{CE}	Chip Enable Access Time		70		90	ns
T_{AA}	Address Access Time		70		90	ns
T_{OE}	Output Enable Access Time		35		45	ns
T_{CLZ}	CE# Low to Active Output	0		0		ns
T_{OLZ}	OE# Low to Active Output	0		0		ns
T_{CHZ}	CE# High to High-Z Output		30		30	ns
T_{OHZ}	OE# High to High-Z Output		30		30	ns
T_{OH}	Output Hold from Address Change	0		0		ns

397 PGM T9.1

TABLE 10: PROGRAM/ERASE CYCLE TIMING PARAMETERS

V_{DD} = 2.7 to 3.6V, T_A = 25°C ± 5°C

Symbol	Parameter	Min	Max	Units
T_{PC}	Program Cycle Time	12		µs
T_{CES}	CE# Setup Time	1		µs
T_{CEH}	CE# Hold Time	1		µs
T_{AS}	Address Setup Time	1		µs
T_{AH}	Address Hold Time	1		µs
T_{DS}	Data Setup Time	1		µs
T_{DH}	Data Hold Time	1		µs
T_{PRT}	OE# Rise Time for Program and Erase	1		µs
T_{VPS}	OE# Setup Time for Program and Erase	1		µs
T_{VPH}	OE# Hold Time for Program and Erase	1		µs
T_{PW}	WE# Program Pulse Width	10	15	µs
T_{EW}	WE# Erase Pulse Width	100	500	ms
T_{VR}	OE#/A_9 Recovery Time for Erase	1		µs
T_{ART}	A_9 Rise Time to 12V during Erase	1		µs
T_{A9S}	A_9 Setup Time during Erase	1		µs
T_{A9H}	A_9 Hold Time during Erase	1		µs

397 PGM T10.0

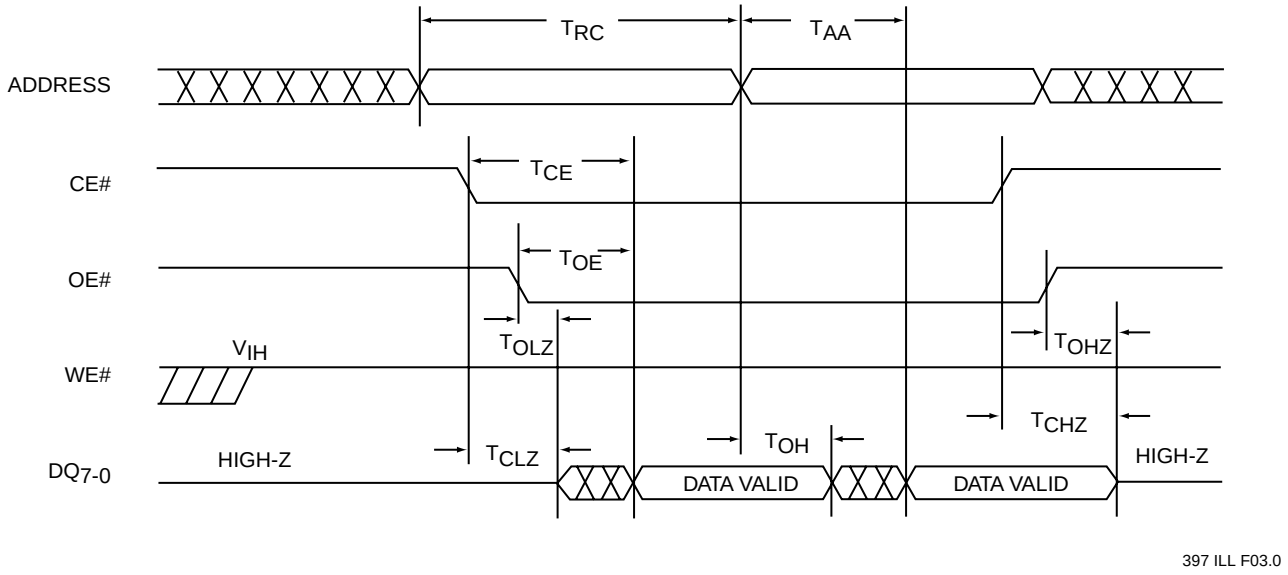


FIGURE 4: READ CYCLE TIMING DIAGRAM

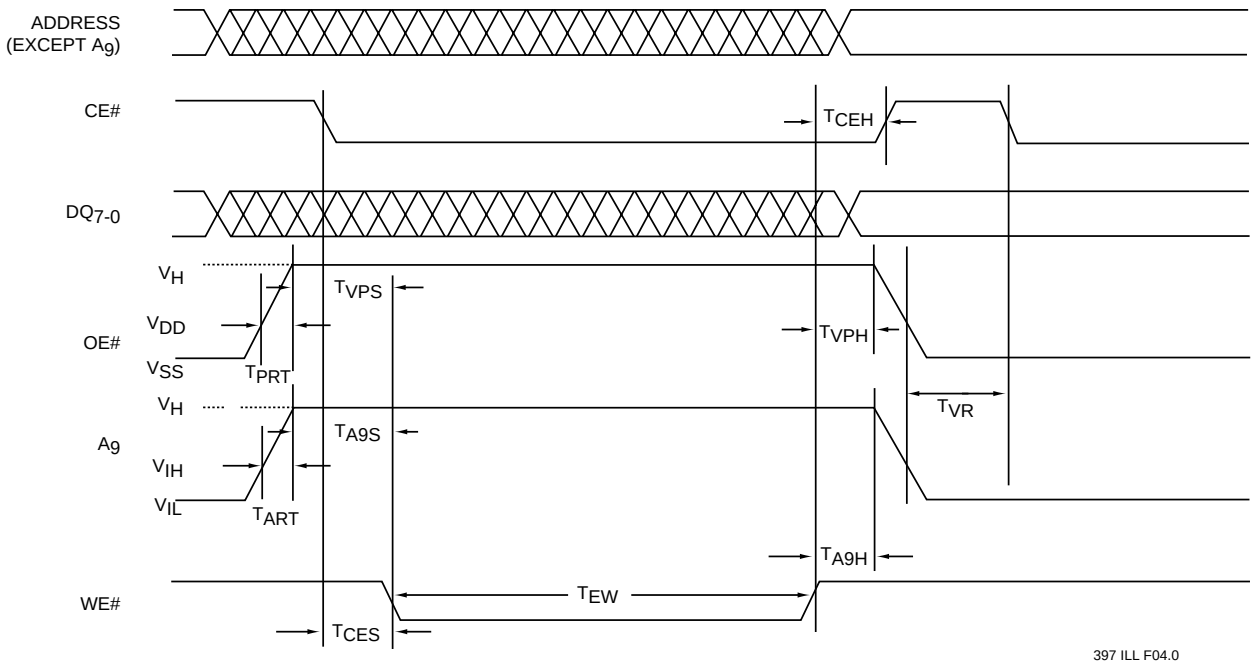


FIGURE 5: CHIP-ERASE TIMING DIAGRAM

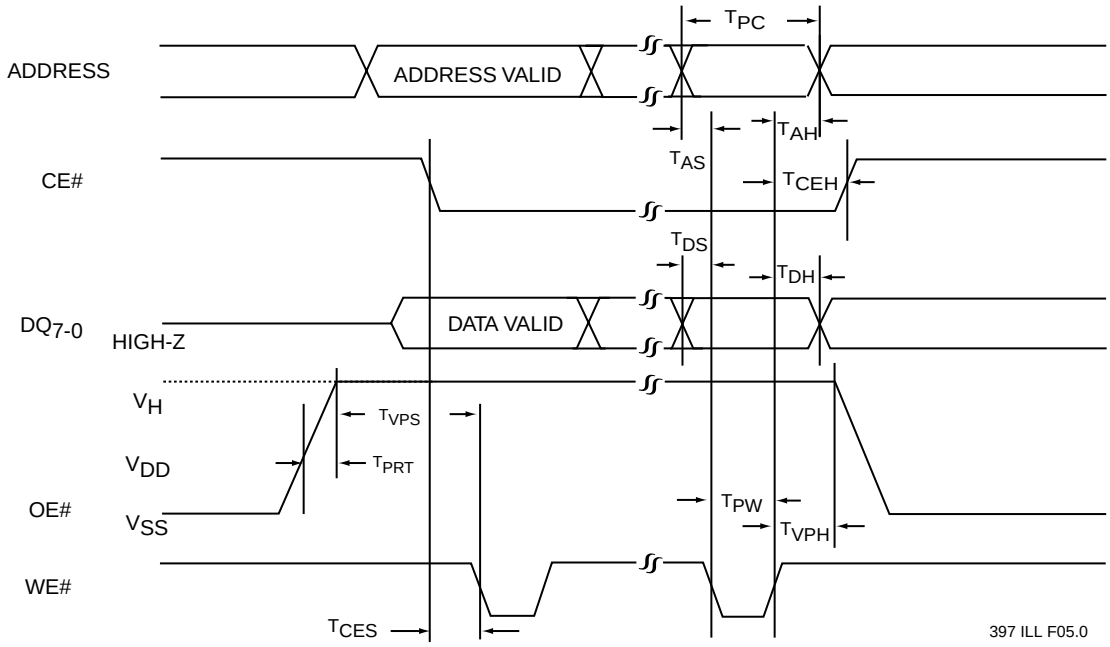
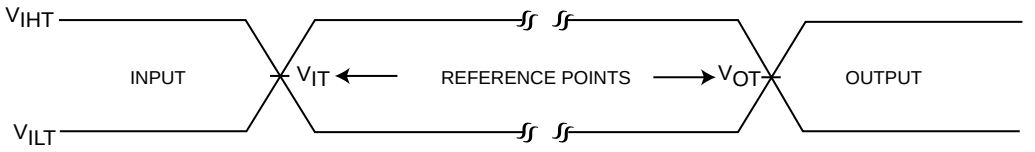


FIGURE 6: BYTE-PROGRAM TIMING DIAGRAM



AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT} (0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outputs are V_{IT} (0.5 V_{DD}) and V_{OT} (0.5 V_{DD}). Inputs rise and fall times (10% ↔ 90%) are <5 ns.

Note: V_{IT}–V_{INPUT} Test
V_{OT}–V_{OUTPUT} Test
V_{IHT}–V_{INPUT} HIGH Test
V_{ILT}–V_{INPUT} LOW Test

FIGURE 7: AC INPUT/OUTPUT REFERENCE WAVEFORMS

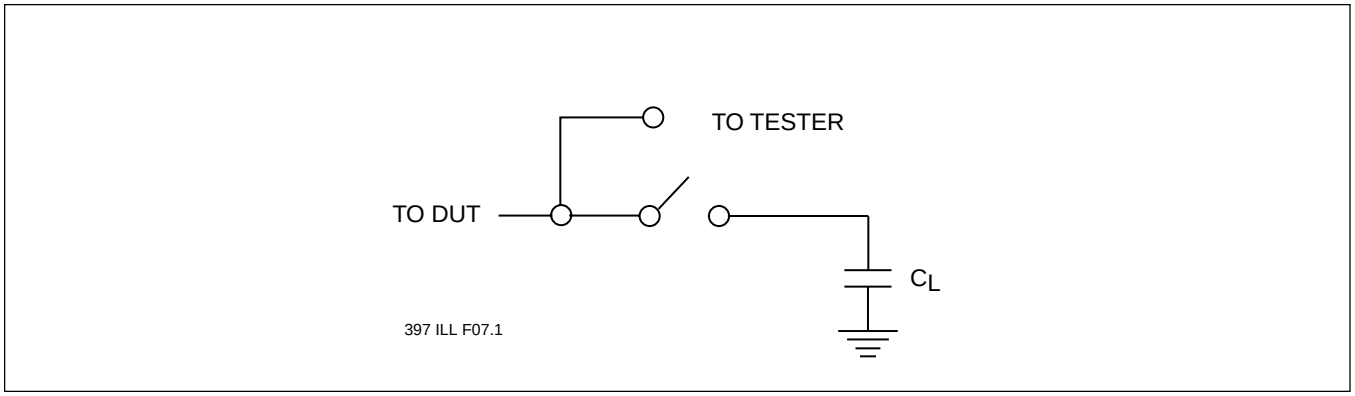


FIGURE 8: A TEST LOAD EXAMPLE

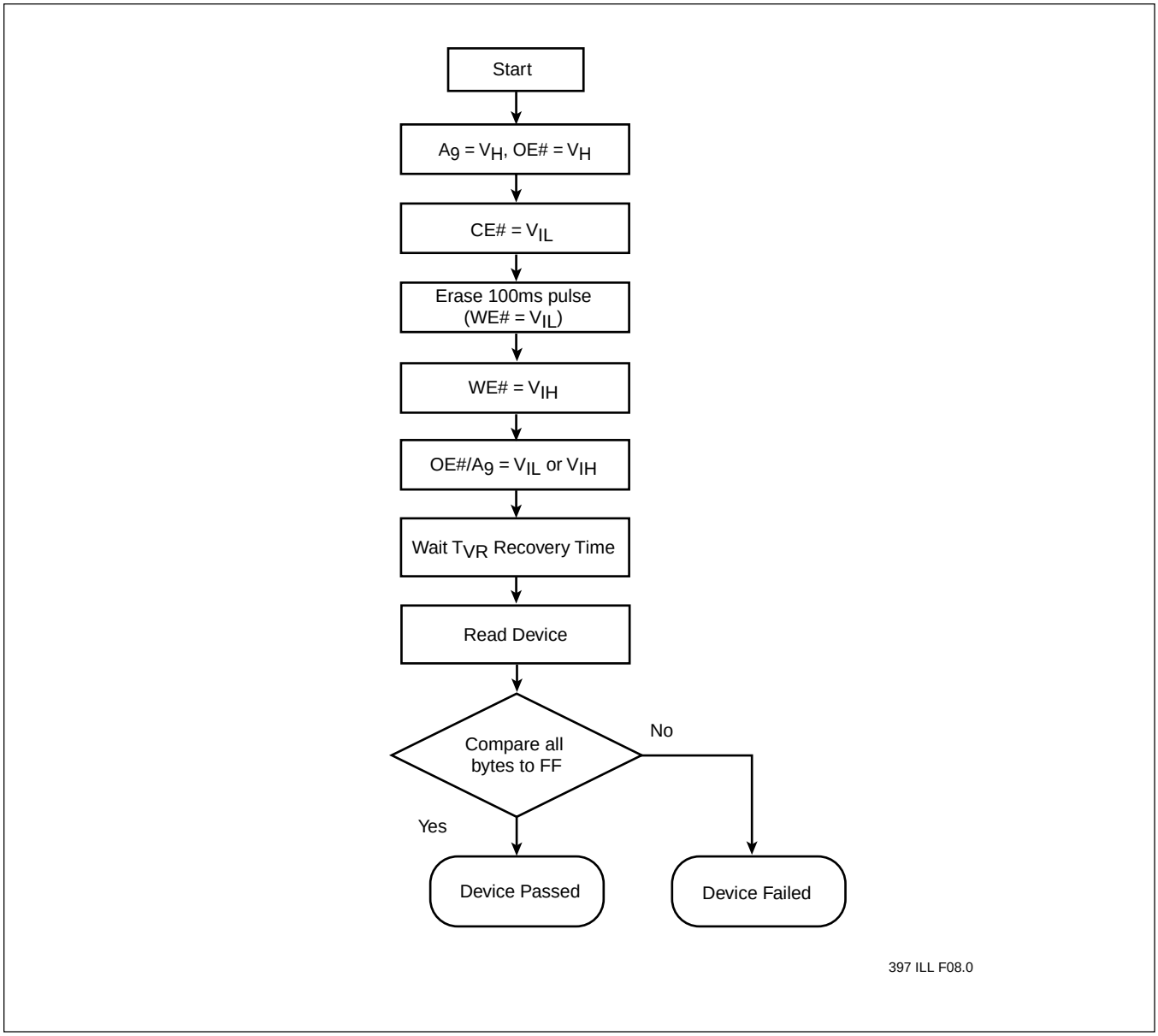


FIGURE 9: CHIP-ERASE ALGORITHM

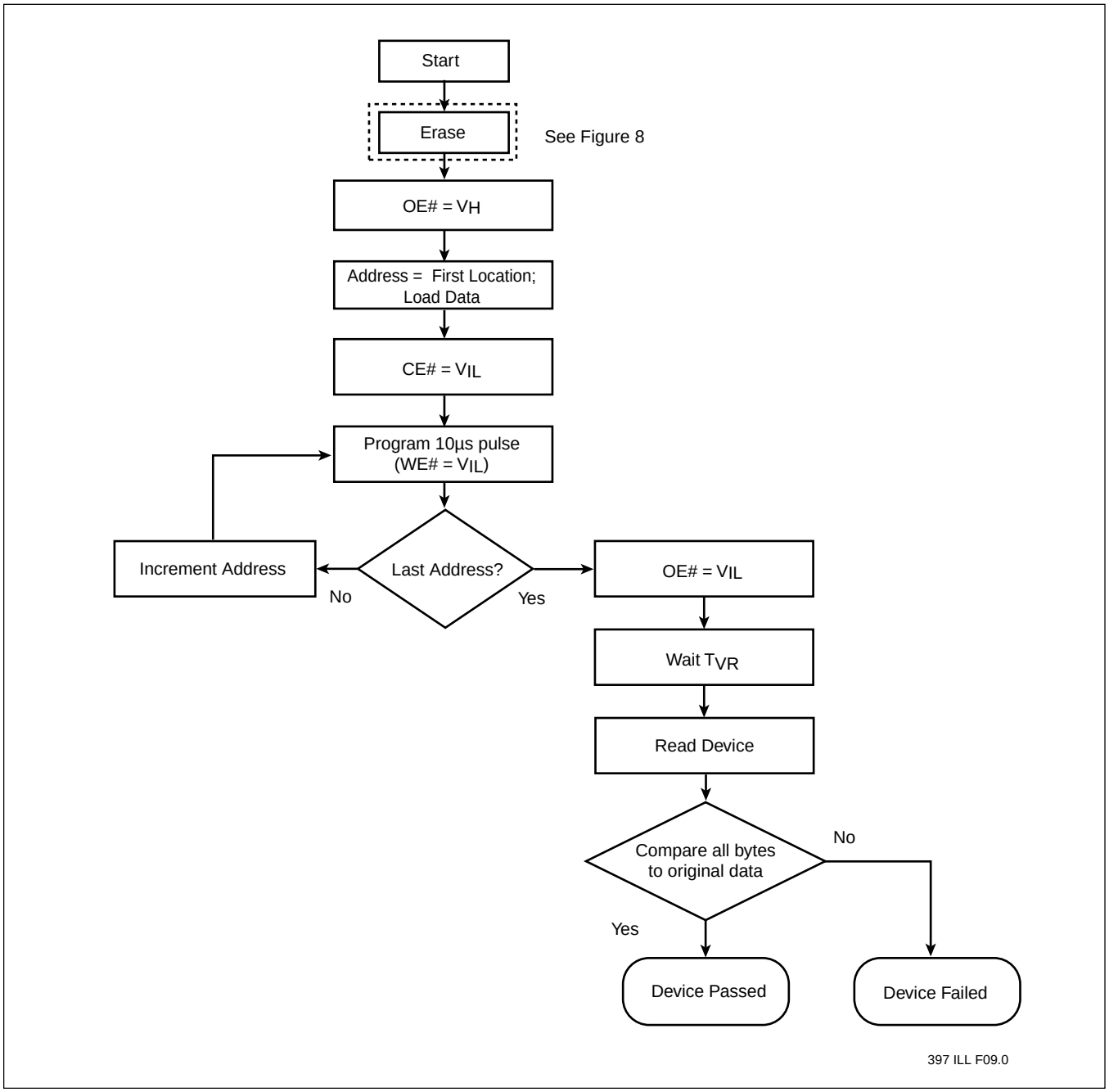
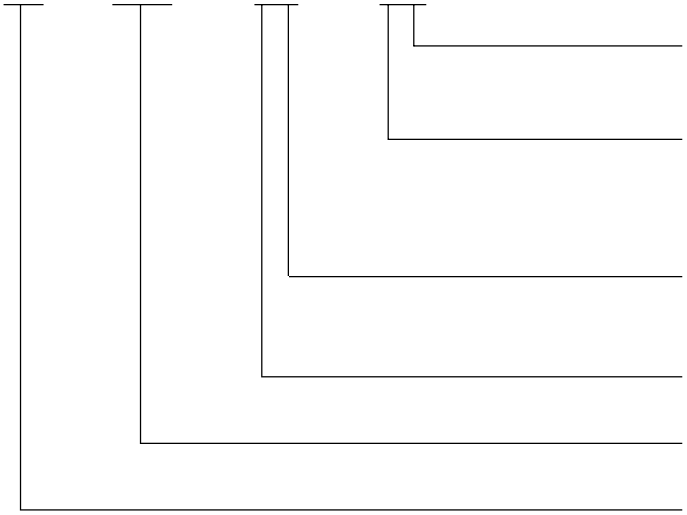


FIGURE 10: BYTE-PROGRAM ALGORITHM

PRODUCT ORDERING INFORMATION

Device **Speed** **Suffix1** **Suffix2**

SST37VFxxx - XXX - XX - XX



Package Modifier
- H = 32 pins
- Numeric = Die modifier

Package Type
- P = PDIP
- N = PLCC
- W = TSOP 8mm x14mm

Operating Temperature
- C = Commercial = 0° to 70°C
- I = Industrial = -40° to 85°C

Minimum Endurance
- 3 = 1000 cycles

Read Access Speed
- 70 = 70 ns, 90 = 90 ns

Device Density
- 512 = 512 Kilobit
- 010 = 1 Megabit
- 020 = 2 Megabit
- 040 = 4 Megabit

SST37VF512 Valid combinations

SST37VF512-70-3C-WH	SST37VF512-70-3C-NH	
SST37VF512-90-3C-WH	SST37VF512-90-3C-NH	SST37VF512-90-3C-PH
SST37VF512-70-3I-WH	SST37VF512-70-3I-NH	
SST37VF512-90-3I-WH	SST37VF512-90-3I-NH	

SST37VF010 Valid combinations

SST37VF010-70-3C-WH	SST37VF010-70-3C-NH	
SST37VF010-90-3C-WH	SST37VF010-90-3C-NH	SST37VF010-90-3C-PH
SST37VF010-70-3I-WH	SST37VF010-70-3I-NH	
SST37VF010-90-3I-WH	SST37VF010-90-3I-NH	

SST37VF020 Valid combinations

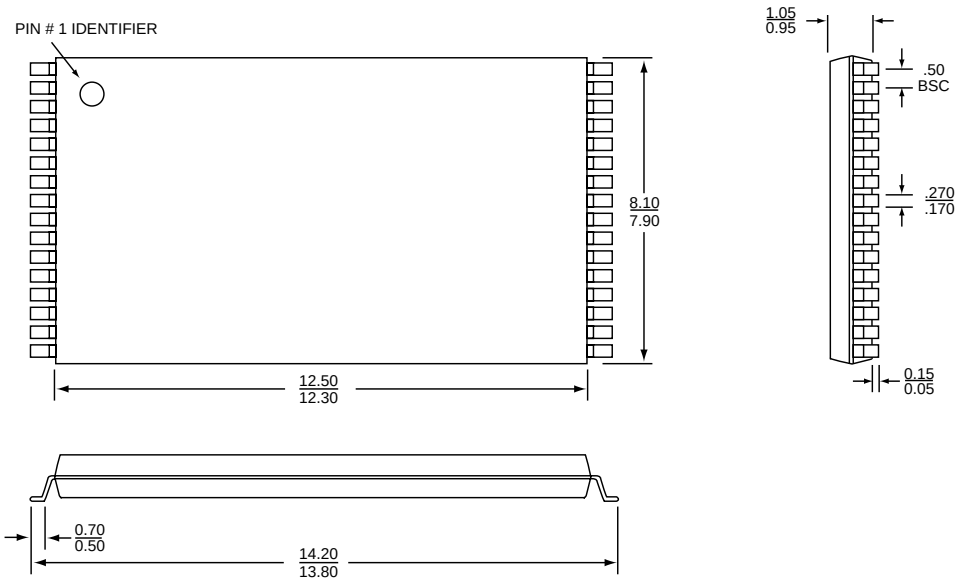
SST37VF020-70-3C-WH	SST37VF020-70-3C-NH	
SST37VF020-90-3C-WH	SST37VF020-90-3C-NH	SST37VF020-90-3C-PH
SST37VF020-70-3I-WH	SST37VF020-70-3I-NH	
SST37VF020-90-3I-WH	SST37VF020-90-3I-NH	

SST37VF040 Valid combinations

SST37VF040-70-3C-WH	SST37VF040-70-3C-NH	
SST37VF040-90-3C-WH	SST37VF040-90-3C-NH	SST37VF040-90-3C-PH
SST37VF040-70-3I-WH	SST37VF040-70-3I-NH	
SST37VF040-90-3I-WH	SST37VF040-90-3I-NH	

Example: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

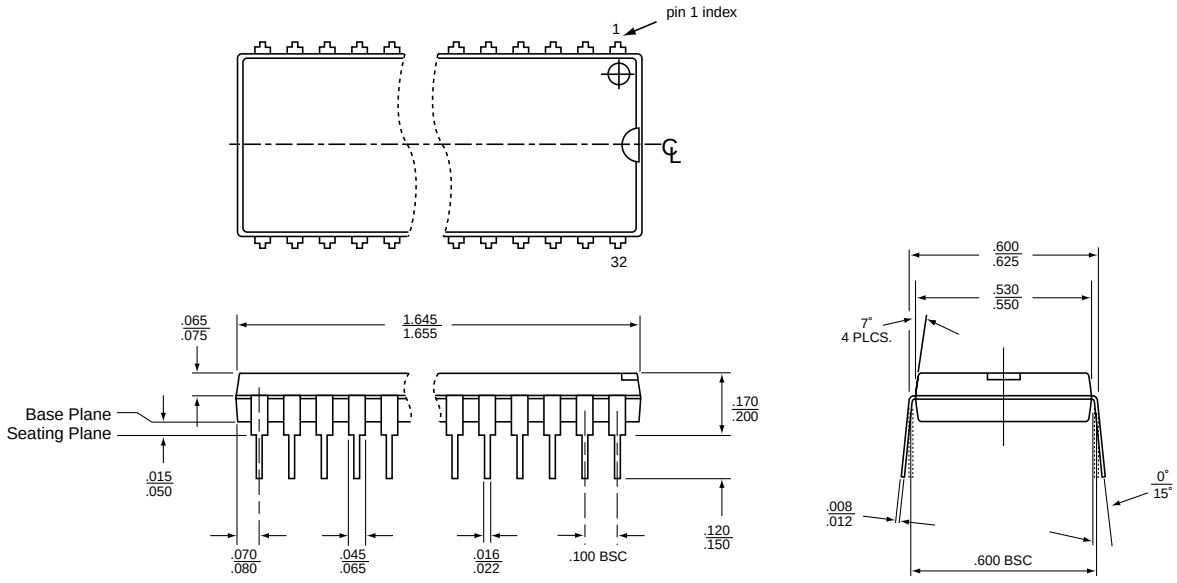
PACKAGING DIAGRAMS



Note: 1. Complies with JEDEC publication 95 MO-142 BA dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in millimeters (min/max).
3. Coplanarity: 0.1 (±.05) mm.

32.TSOP-WH-ILL.3

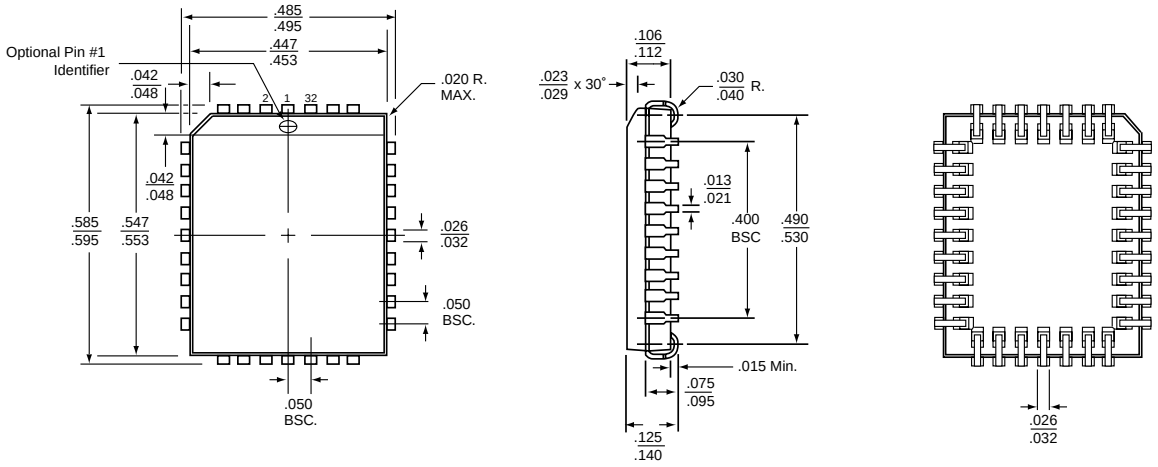
32-PIN THIN SMALL OUTLINE PACKAGE (TSOP)
SST PACKAGE CODE: WH



Note: 1. Complies with JEDEC publication 95 MO-015 AP dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in inches (min/max).
3. Dimensions do not include mold flash. Maximum allowable mold flash is .010 inches.

32.pdipPH-ILL.1

32-PIN PLASTIC DUAL-IN-LINE PACKAGE (PDIP)
SST PACKAGE CODE: PH



Note: 1. Complies with JEDEC publication 95 MS-016 AE dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in inches (min/max).
3. Dimensions do not include mold flash. Maximum allowable mold flash is .008 inches.

32.PLCC.NH-ILL.1

32-PIN PLASTIC LEAD CHIP CARRIER (PLCC)
SST PACKAGE CODE: NH